

Abstract of the Invention

A method for Chemical-Mechanical Polishing utilizes a two step process. The first step utilizes a slurry with abrasive particles which become embedded into a conditioned polishing pad having small cavities in the surface. During the second step the slurry flow is discontinued and the final polishing is performed using the embedded small abrasive particles. Using this method dishing has been reduced considerably, and has enabled the fabrication of a Damascene metal gate NMOSFET fabricated with Atomic Layer Deposition (ALD).

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